

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different in electric characteristics by applying at least a voltage or a current,

wherein a memory cell is formed that stores 1-bit data by using two states that one memory element is in the first state and the other memory element is in the second state.

2. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different in electric characteristics by applying at least a voltage or a current,

wherein a memory cell is formed that stores data by using only a state that a certain number of memory elements transit from the first state to the second state.

3. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different in electric characteristics by applying a voltage or a current,

wherein a memory cell is formed that stores 1-bit data by using two states that cannot be transited to each other by applying a voltage to the first memory element or the second memory element.

4. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different in electric characteristics by applying at least a voltage or a current,

wherein a memory cell is formed that stores data by using only a state that cannot be transited to each other among combinations obtained in the unit.

5. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different from a threshold voltage by applying a voltage,

wherein a memory cell is formed that stores 1-bit data by using two states that one memory element is in the first state and the other memory element is in the second state.

6. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different from a threshold voltage by applying a voltage,

wherein a memory cell is formed that stores data by using only a state that a certain number of the memory elements transit from the first state to the second state.

7. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different from a threshold voltage by applying a voltage,

wherein a memory cell is formed that stores 1-bit data by using two states that cannot be transited to each other by applying a voltage to the pair of memory elements among four states that can be obtained by the pair of memory elements.

8. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different from a threshold voltage by applying a voltage,

wherein a memory cell is formed that stores data by using only a state that cannot be transited to each other among states that can be obtained in the unit.

9. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different from a resistance value by applying a current,

wherein a memory cell is formed that stores 1-bit data by using two states that one memory element is in the first state and the other memory element is in the second state.

10. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different from a resistance value by applying a current,

wherein a memory cell is formed that stores data by using only a state that a certain number of the memory elements transit from the first state to the second state.

11. (Original) A nonvolatile memory comprising a pair of memory elements as a unit that can transit only from a first state to a second state that are different from a resistance value by applying a current,

wherein a memory cell is formed that stores 1-bit data by using two states that cannot be transited to each other by applying a current to the pair of memory elements among four states that can be obtained by the pair of memory elements.

12. (Original) A nonvolatile memory comprising at least three memory elements as one unit that can transit only from a first state to a second state that are different from a resistance value by applying a current,

wherein a memory cell is formed that stores data by using only a state that cannot be transited to each other among combinations obtained in the unit.

13. (Original) The nonvolatile memory according to any one of claims 1 to 12, wherein a unit for outputting a signal for determining if the memory cell stores data or not is provided.

14. (Original) The nonvolatile memory according to claim 5 or 8, wherein the memory element has a charge accumulating layer comprising a polycrystalline silicon film, a microcrystalline silicon film, a metal film, a microcrystalline metal film, or a nitride film.

15. (Currently Amended) An IC card incorporated with the nonvolatile memory according to any one of claims 1 to [[14]] 12.

16. (Currently Amended) An ID card incorporated with the nonvolatile memory according to any one of claims 1 to [[14]] 12

17. (Currently Amended) An ID tag incorporated with the nonvolatile memory according to any one of claims 1 to [[14]] 12.